

Amendments to the Claims

The claims have been amended as follows. Underlines indicate insertions and ~~strikeouts~~ indicate deletions.

Claims 1-75 (Cancelled).

SUB
FI 7

E1

76. (Currently amended) A DRAM construction, comprising:
a pair of wordlines over a substrate, the wordlines comprising sidewall edges;
carbon-containing sidewall spacers extending along the sidewall edges of the
wordlines, the carbon-containing sidewall spacers consisting essentially of silicon, oxygen
and from about 2% to about 20% carbon, by weight;
three nodes proximate the wordlines, the three nodes comprising a first node,
second node and third node, the second node being in gated electrical connection with the
first node through one of the wordlines and being in gated electrical connection with the
third node through the other of the wordlines;
~~a carbon-containing material proximate the wordlines, the carbon-containing~~
~~material comprising from about 2% to about 20% carbon, and being essentially free of~~
~~nitrogen;~~
an insulative layer over in contact with at least one of the carbon-comprising sidewall
spacers ~~carbon-containing material;~~
a first capacitor construction in electrical connection with the first node, the first
capacitor construction comprising a first storage node;

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a second capacitor construction in electrical connection with the third node, the second capacitor construction comprising a second storage node; and
a bit line contact in electrical connection with the second node, ~~at least one~~ each of the first storage node, second storage node and bit line contact being in physical contact with one or more of the carbon-containing sidewall spacers material.

✓
Claims 77-80. (Cancelled)

E2
81. (Currently amended) The DRAM construction of claim 76 wherein the carbon-containing sidewall spacers comprise ~~material comprises~~ silicon carbide.

✓
Claims 83-94. (Cancelled) ✓

E3
95. (New) The DRAM construction of claim 76 wherein the carbon-containing sidewall spacers have a thickness of less than about 500 Å.

F
96. (New) The DRAM construction of claim 76 wherein the insulative layer comprises borophosphosilicate glass.
